

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Technical Note

Specifications are subject to change without notice.

DESCRIPTION

The MGF7169C is a monolithic microwave integrated circuit for use in CDMA base handheld phone.

FEATURES

- Low voltage operation :
Vd=3.0V
- High output power :
Po=28dBm typ. @f=1.85~1.91GHz
- Low distortion :
ACP=-46dBc max. @Po=28dBm
- High efficiency :
Id=520mA typ. @Po=28dBm
- Small size :
7.0 x 6.1 x 1.1 mm
- Surface mount package
- 2 Stage Amplifier
- External matching circuit is required

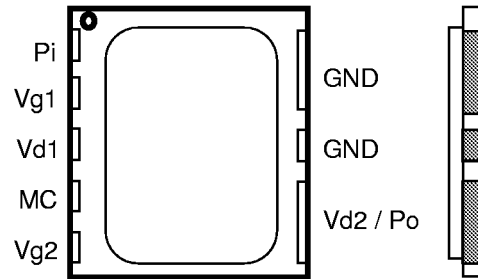
APPLICATION

1.9GHz band handheld phone

QUALITY GRADE

GG

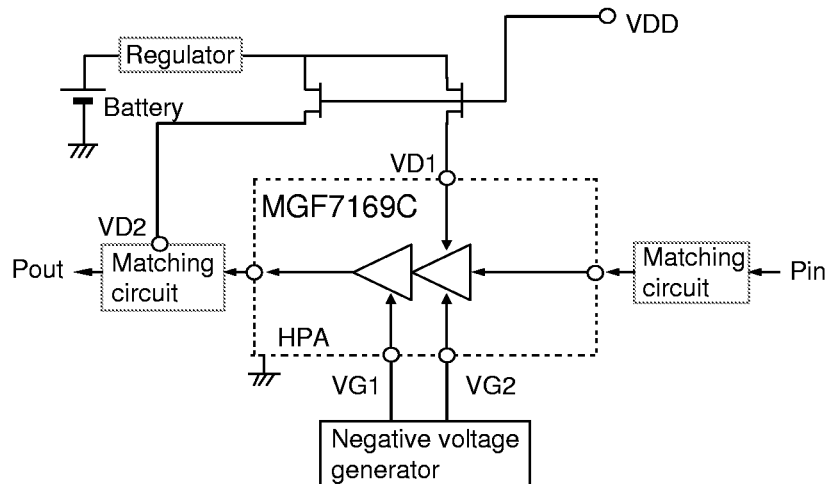
PIN CONFIGURATION (TOP VIEW)



- Pi : RF input
- Po : RF output
- Vd1 : Drain bias 1
- Vd2 : Drain bias 2
- Vg : Gate bias
- MC : Note1
- GND : Connect to GND
- CASE: Connect to GND

Note1: Connect to matching circuit

Block Diagram of this IC and Application Circuit Example.



*Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary, circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
Vd1,Vd2	Drain supply voltage	6	V
Vg	Gate supply voltage	-4	V
Pi	Input power	15	dBm
Tc(op)	Operating case temperature	-30 ~ +85	°C
Tstg	Storage temperature	-30 ~ +100	°C

*1.Each maximum rating is guaranteed independently.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			MIN	TYP	MAX	
f	frequency		1850	—	1910	MHz
Idt	Total drain current	ACP<-42dBc (1.25MHz off-set.) Vd1=Vd2=3.0V	—	450	—	mA
		ACP<-44dBc (1.25MHz off-set.) Vd1=Vd2=3.0V	—	480	—	
		ACP<-46dBc (1.25MHz off-set.) Vd1=Vd2=3.0V	—	520	—	
		ACP<-44dBc (1.25MHz off-set.) Vd1=Vd2=3.3V	—	450	—	
Idle_Id	Idle current	Vg1=Vg2=-2.0V, Po=28dBm	—	150	—	mA
		Vg1=Vg2=-2.5V, Po=12dBm	—	50	—	
Pout	Output power		—	28	—	dBm
Ig	Gate current	Vd1=Vd2=3.0V, Vg1=Vg2=-2.0V, Pin=7dBm CDMA modulated signal based on IS-95 STD. (1.2288Mbps spreading, OQPSK)	—	—	-3	mA
2sp	2nd harmonics		—	—	-30	dBc
rin	input VSWR		—	—	3	—
—	Damage with-standing Note	Vd1=Vd2=3.0V, Pin=7dBm, Load VSWR=10, All phase Time=10 sec	No damage			
—	Stability Note	Vd1=Vd2=3.0V, Pin=7dBm, Load VSWR=3:1, All phase	No oscillation Spurious level≤-60dBc			

*CDMA is code division multiple Access. OQPSK is modulation method, off-set quadrature phase shift keying.

Electrical characteristics are changed by the external matching circuit.

Limits are guaranteed by using MITSUBISHI test fixture.

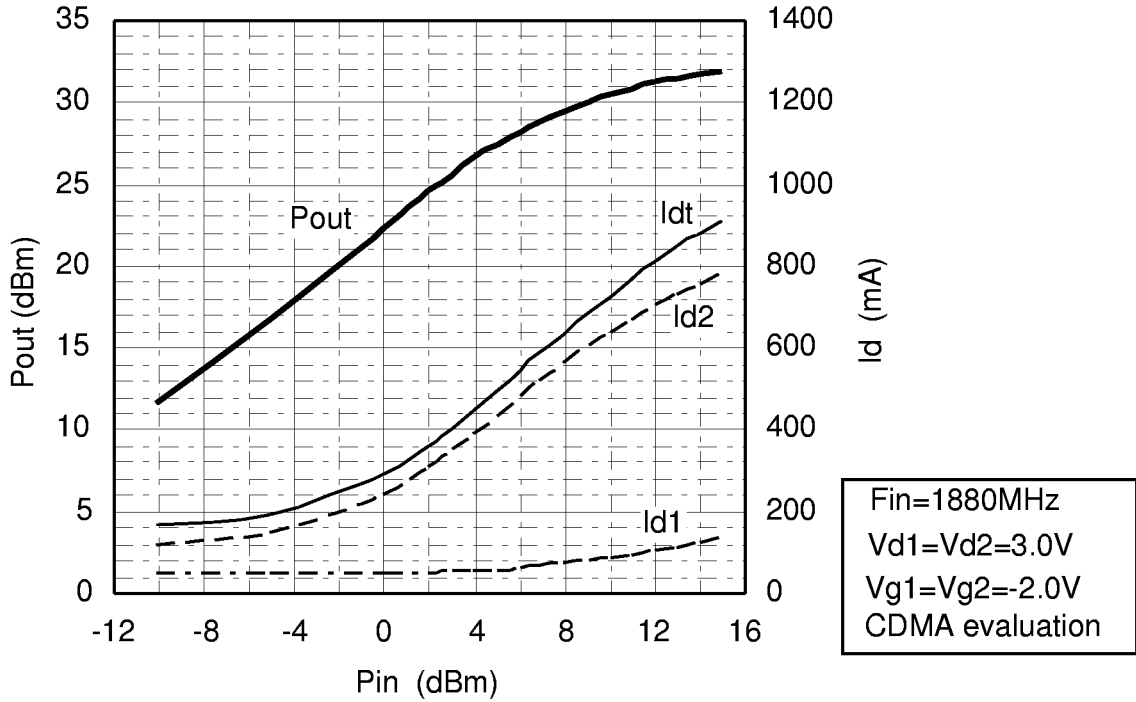
Note : Sampling inspection

Preliminary information

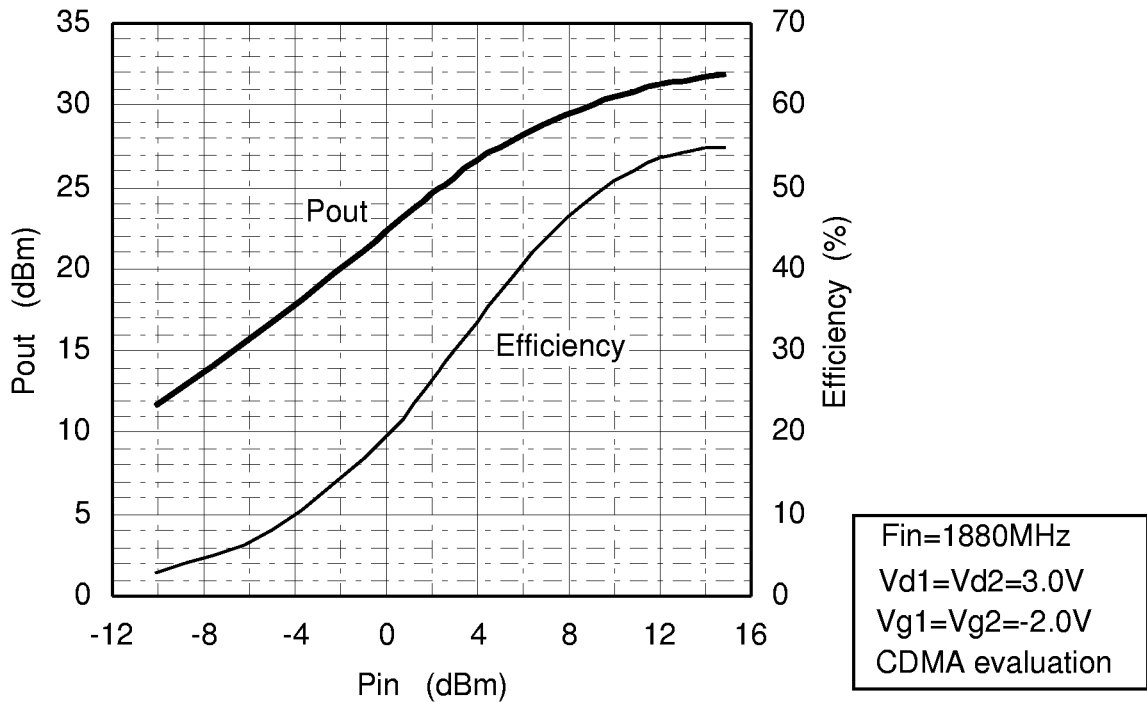
MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Pin vs. Pout, Id for CDMA



Pin vs. Pout, Efficiency for CDMA

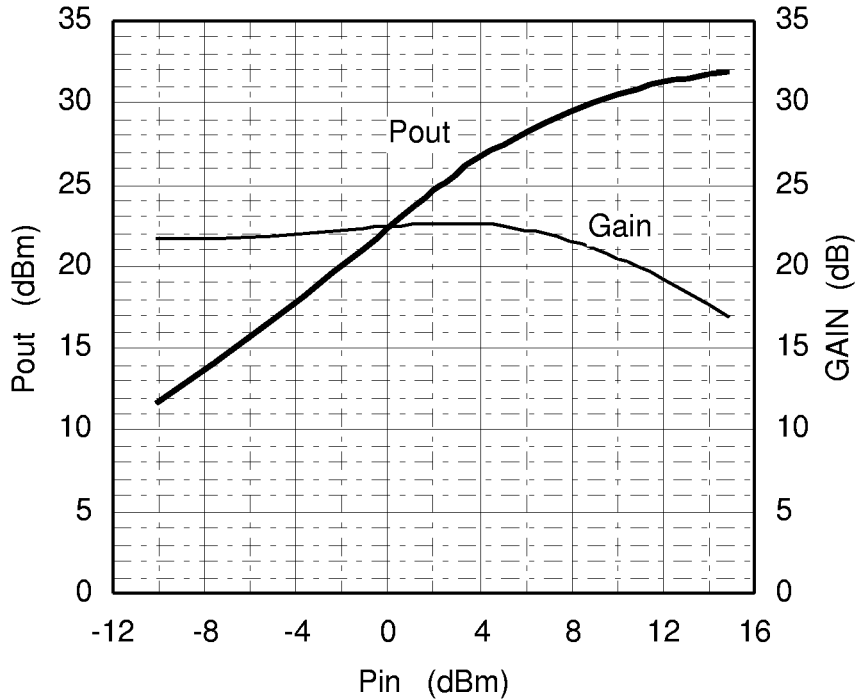


Preliminary information

MGF7169C

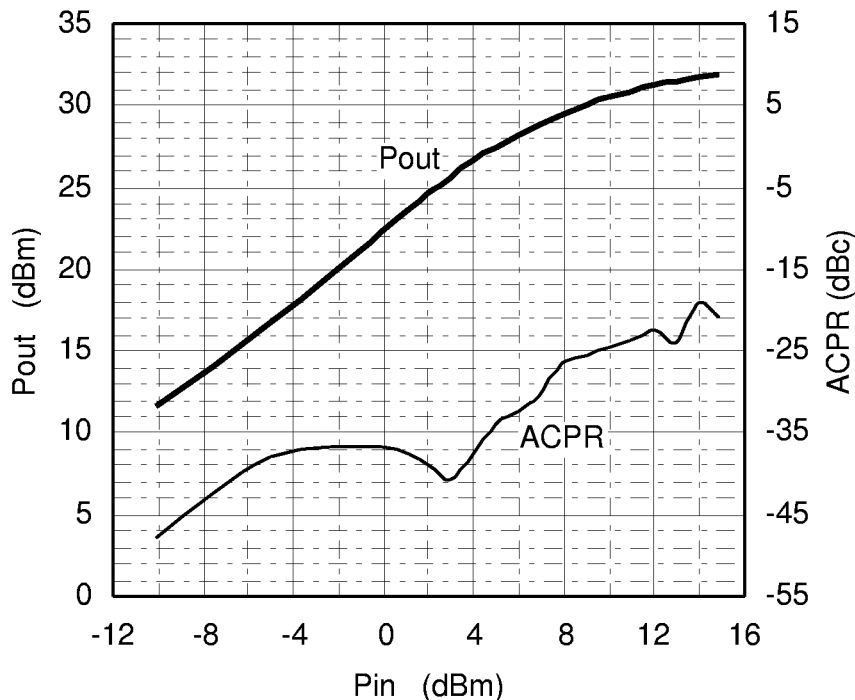
UHF BAND GaAs POWER AMPLIFIER

Pin vs. Pout, Gain for CDMA



Fin=1880MHz
 Vd1=Vd2=3.0V
 Vg1=Vg2=-2.0V
 CDMA evaluation

Pin vs. Pout, ACPR for CDMA



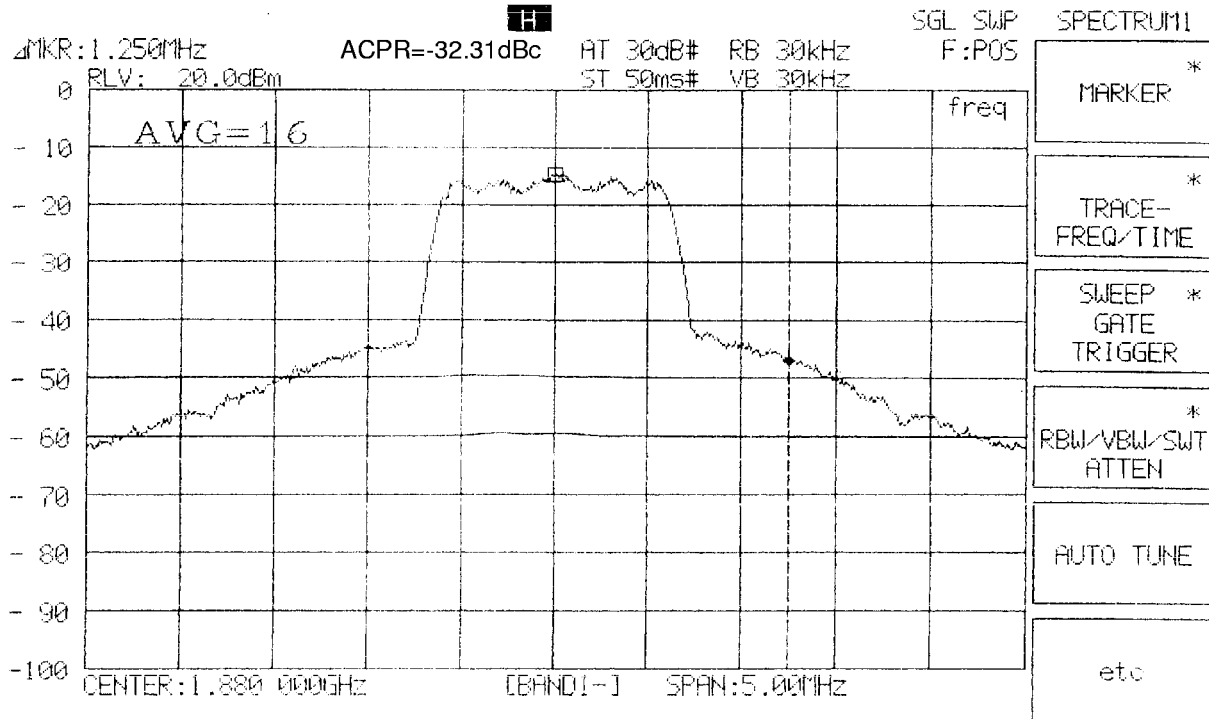
Fin=1880MHz
 Vd1=Vd2=3.0V
 Vg1=Vg2=-2.0V
 CDMA evaluation

Preliminary information

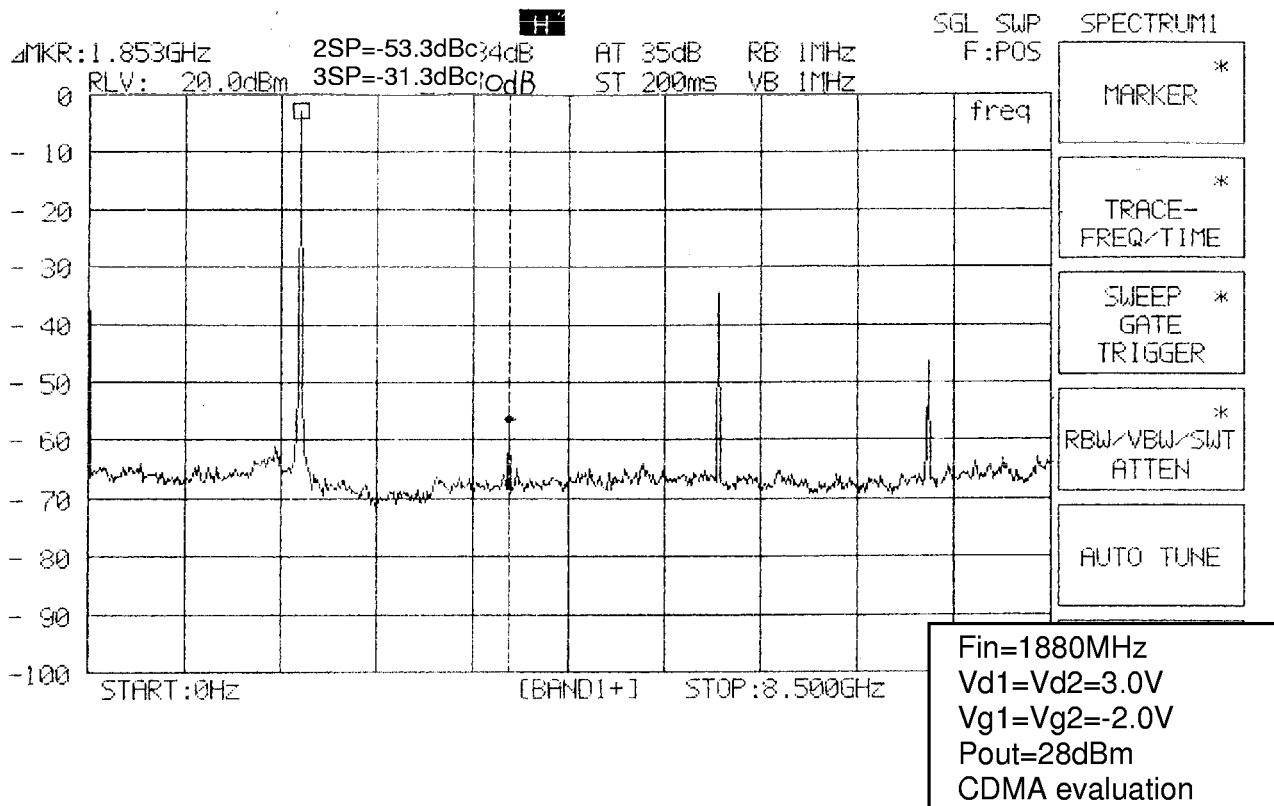
MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Spectral Plot of CDMA



Harmonics

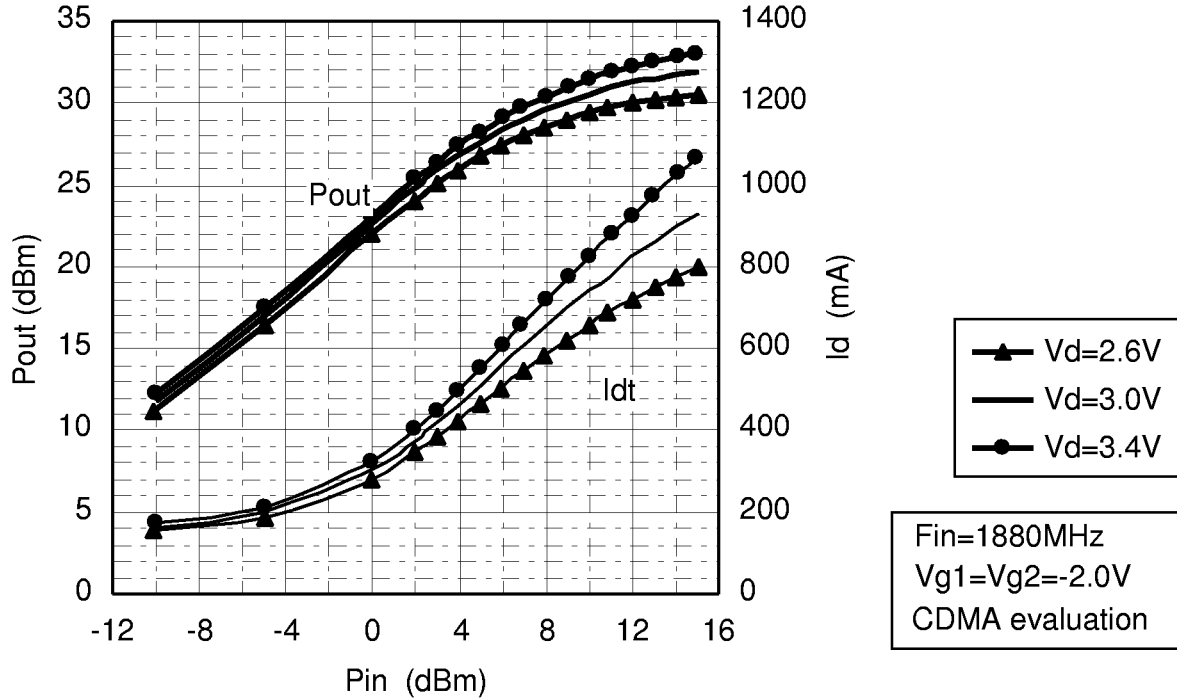


Preliminary information

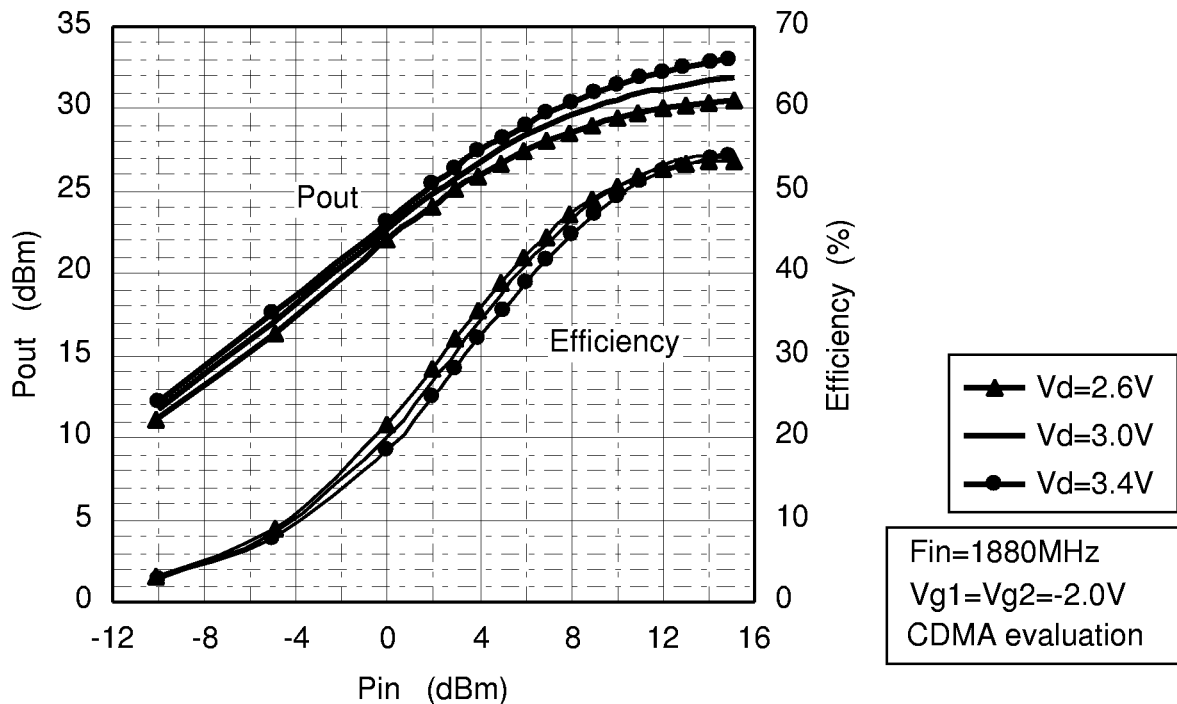
MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Vd dependence of Pin vs.Pout,Idt



Vd dependence of Pin vs.Pout,Efficiency

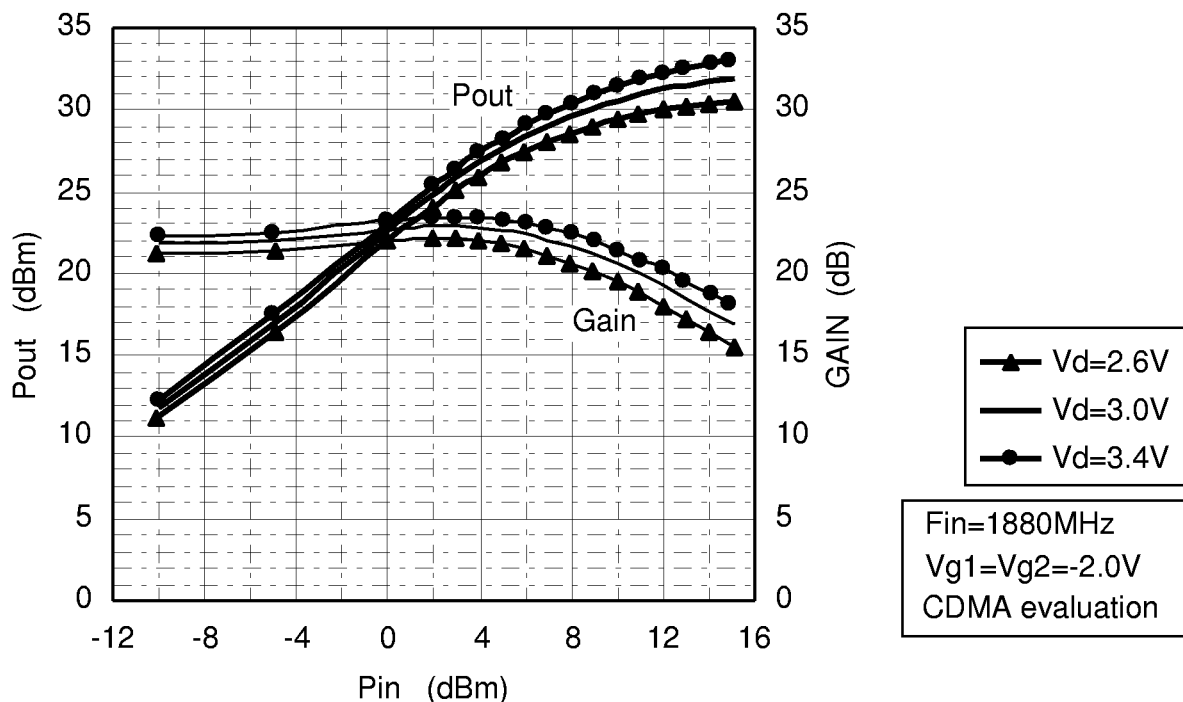


Preliminary information

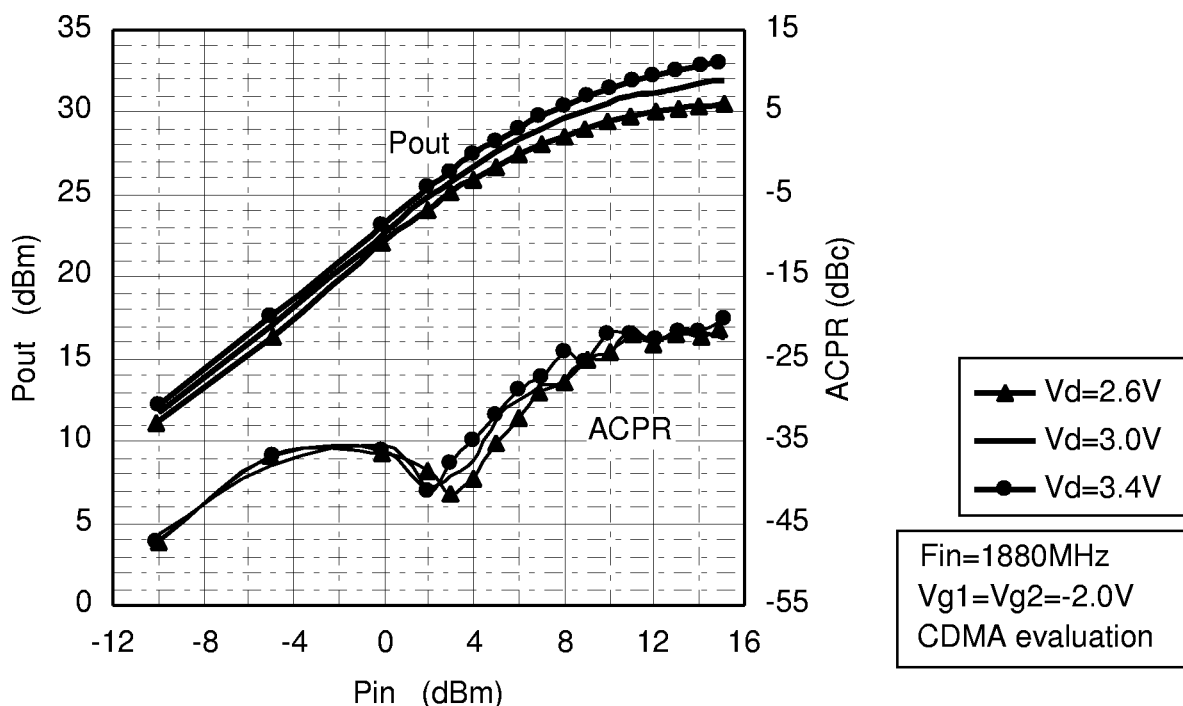
MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Vd dependence of Pin vs.Pout,Gain



Vd dependence of Pin vs.Pout,ACPR

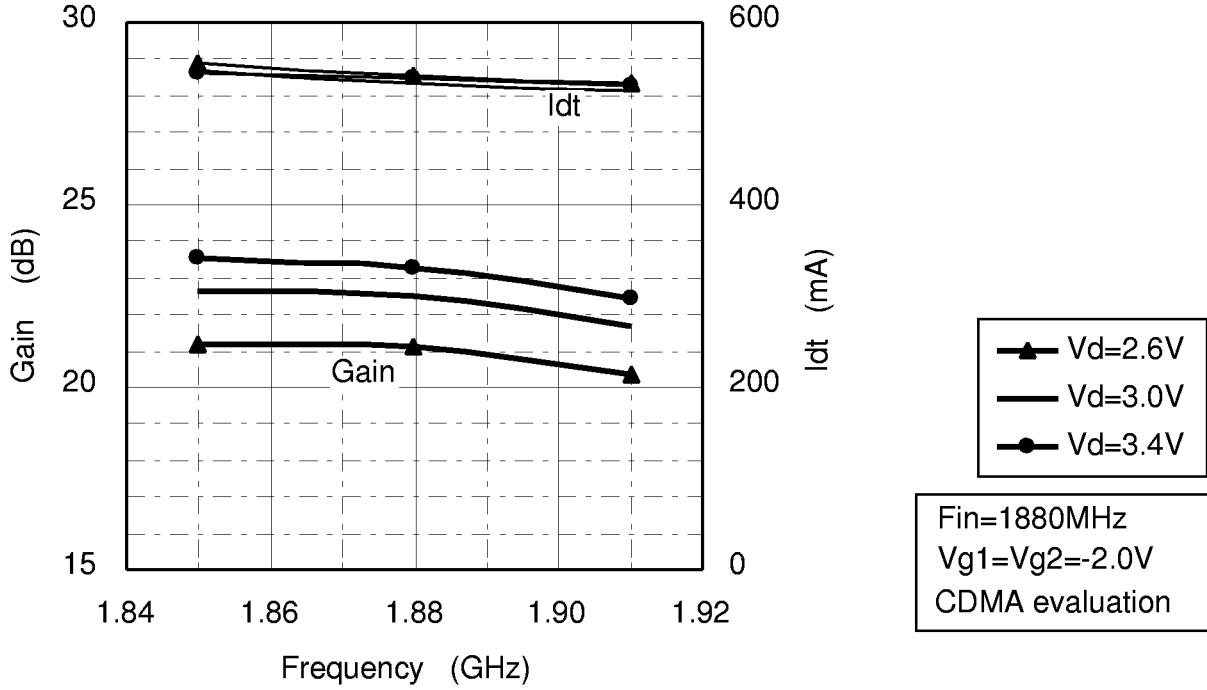


Preliminary information

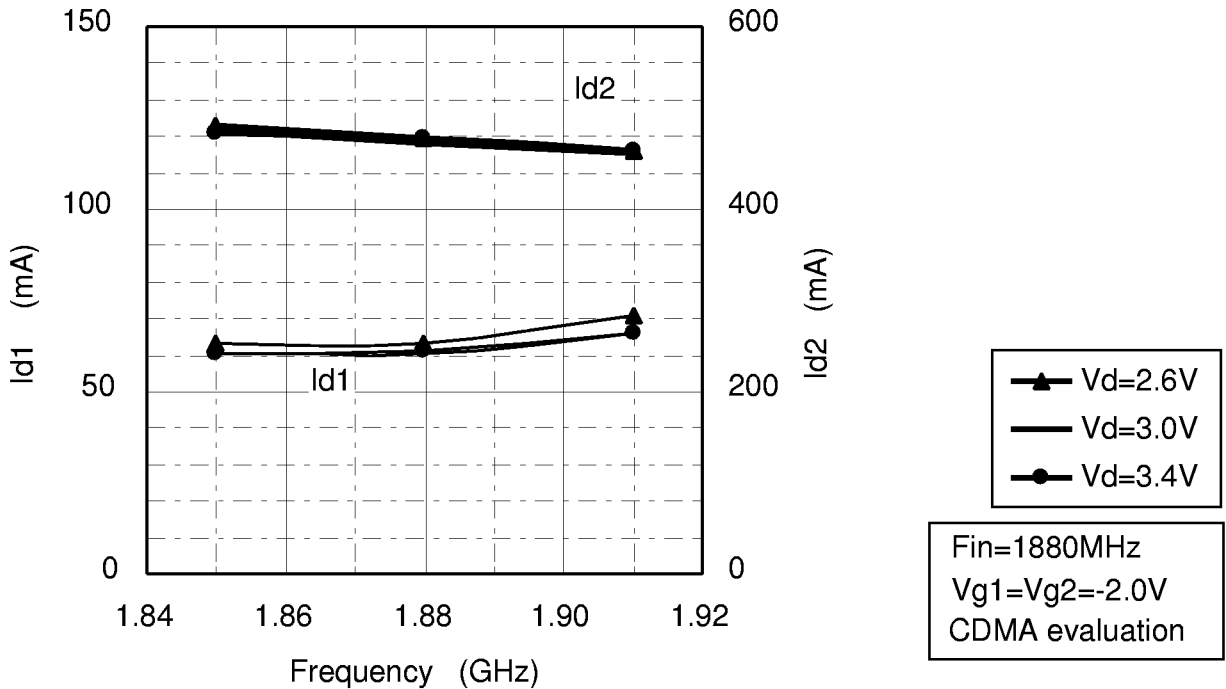
MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Vd dependence of Fin vs. Gain, Idt



Vd dependence of Fin vs. Id1, Id2

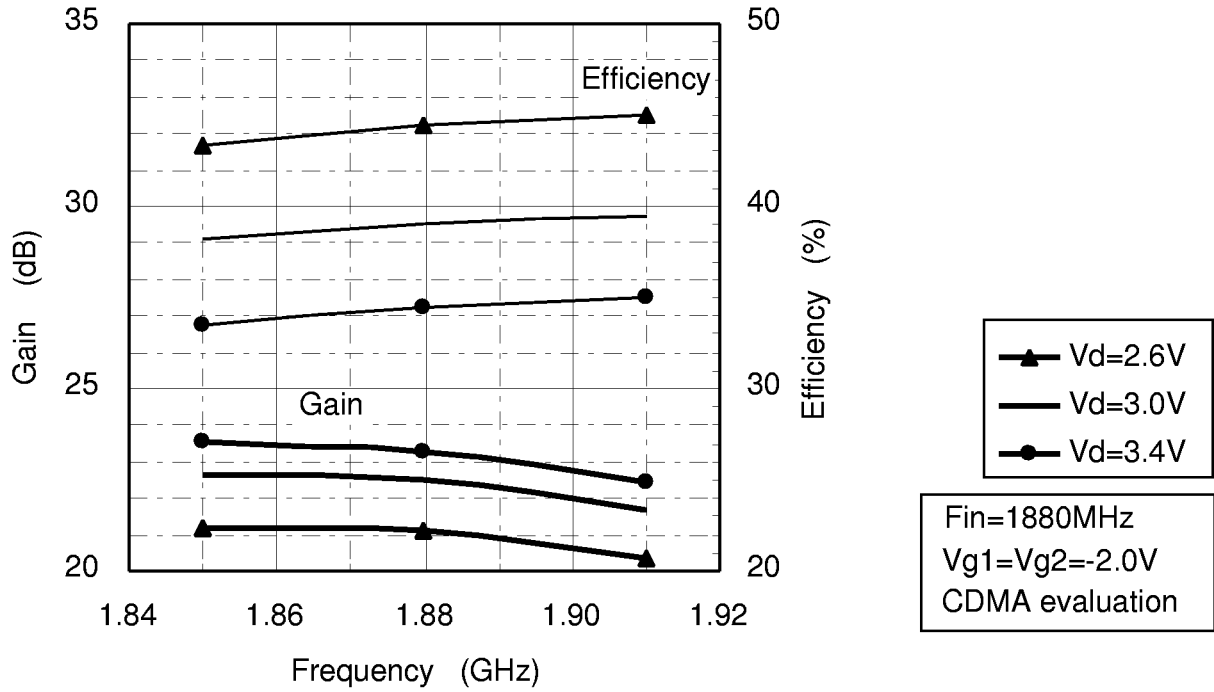


Preliminary information

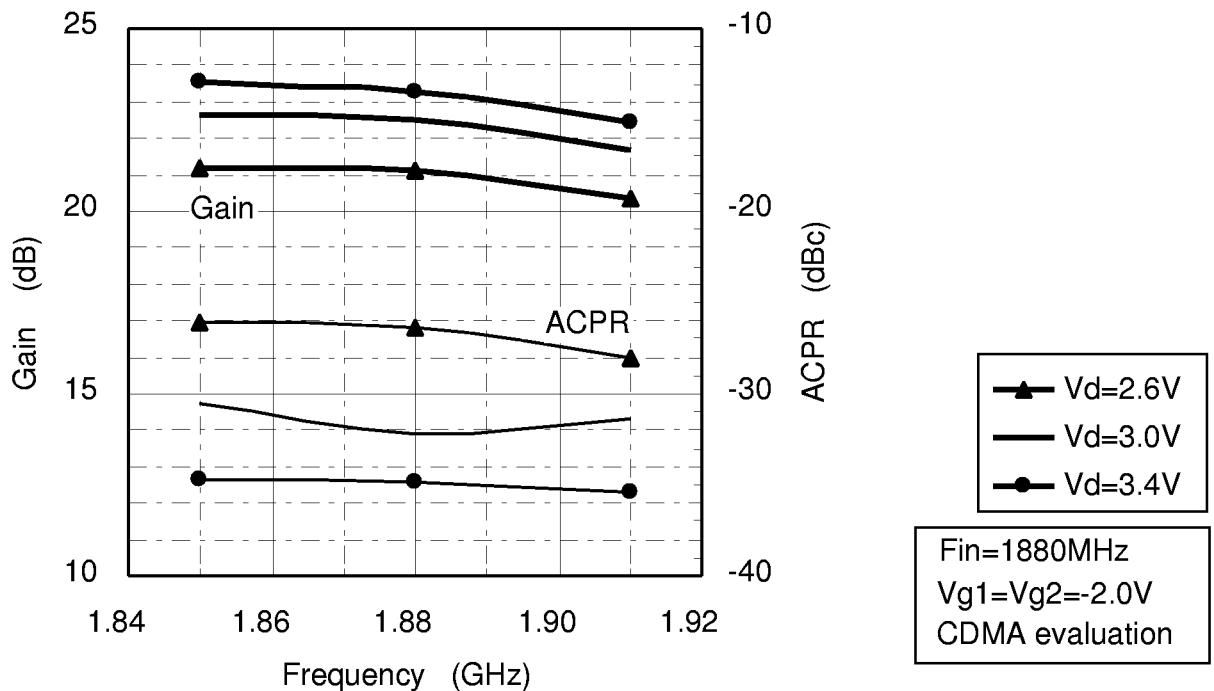
MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Vd dependence of Fin vs. Gain, Efficiency



Vd dependence of Fin vs. Gain, ACPR

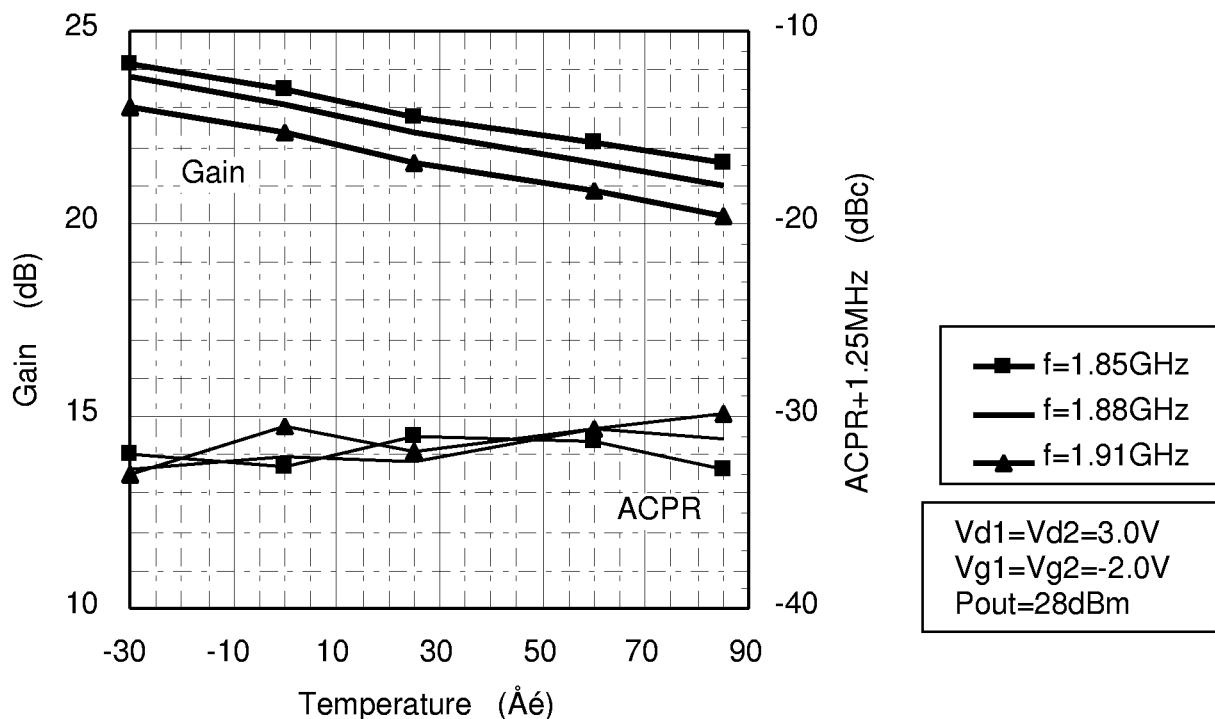


Preliminary information

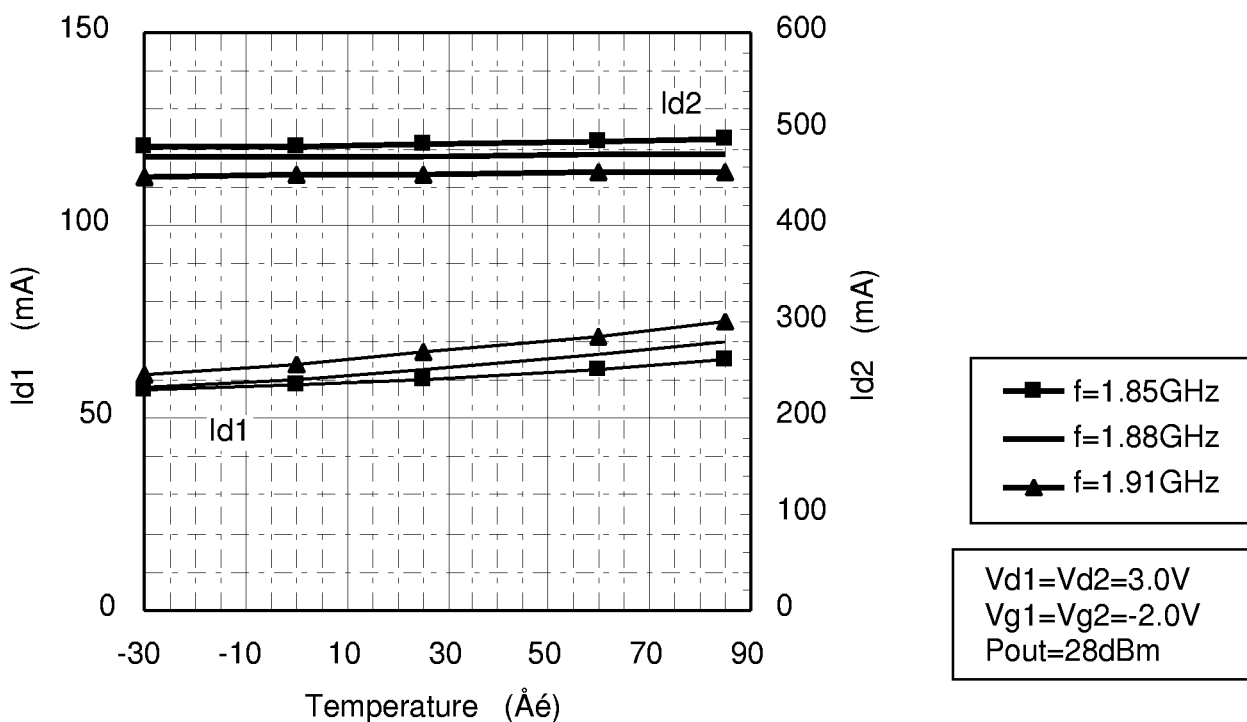
MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Temp. dependence of Fin vs. Gain, ACPR



Temp. dependence of Fin vs. Id1, Id2

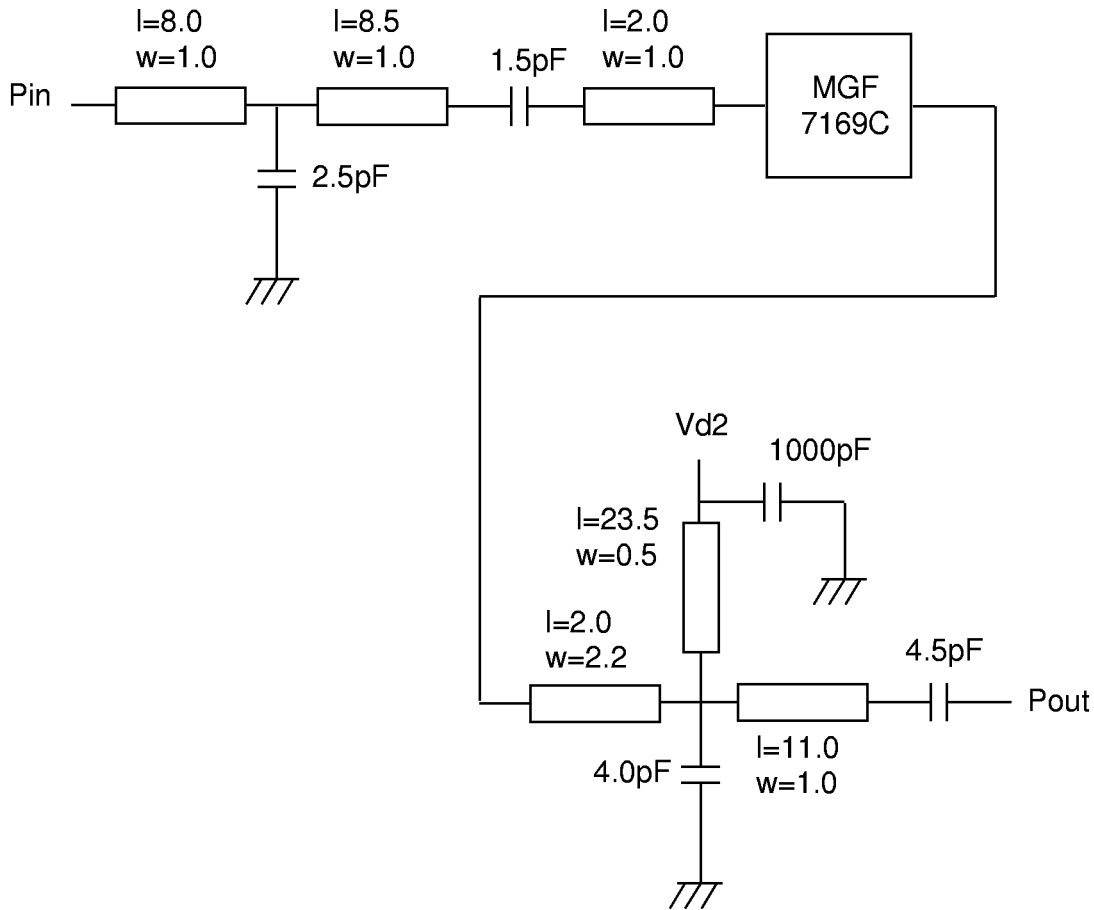


Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Equivalent Circuit of Test Board for CDMA(1.85-1.91GHz)



Unit:mm

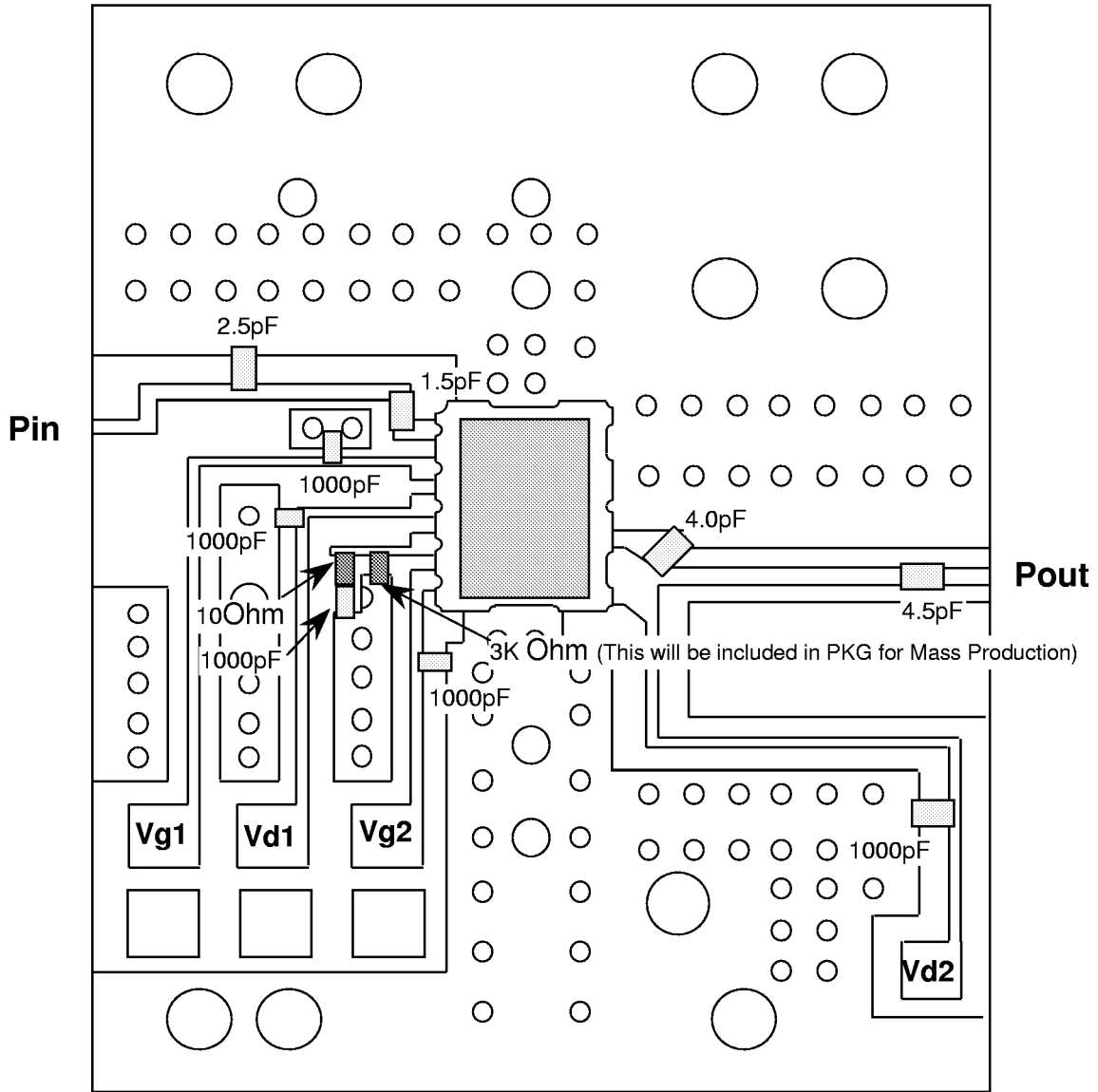
SUB. data
Er=4.8
H=600 mm
Metal T=43 mm

Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Test Circuit Board for CDMA(1.85-1.91GHz)



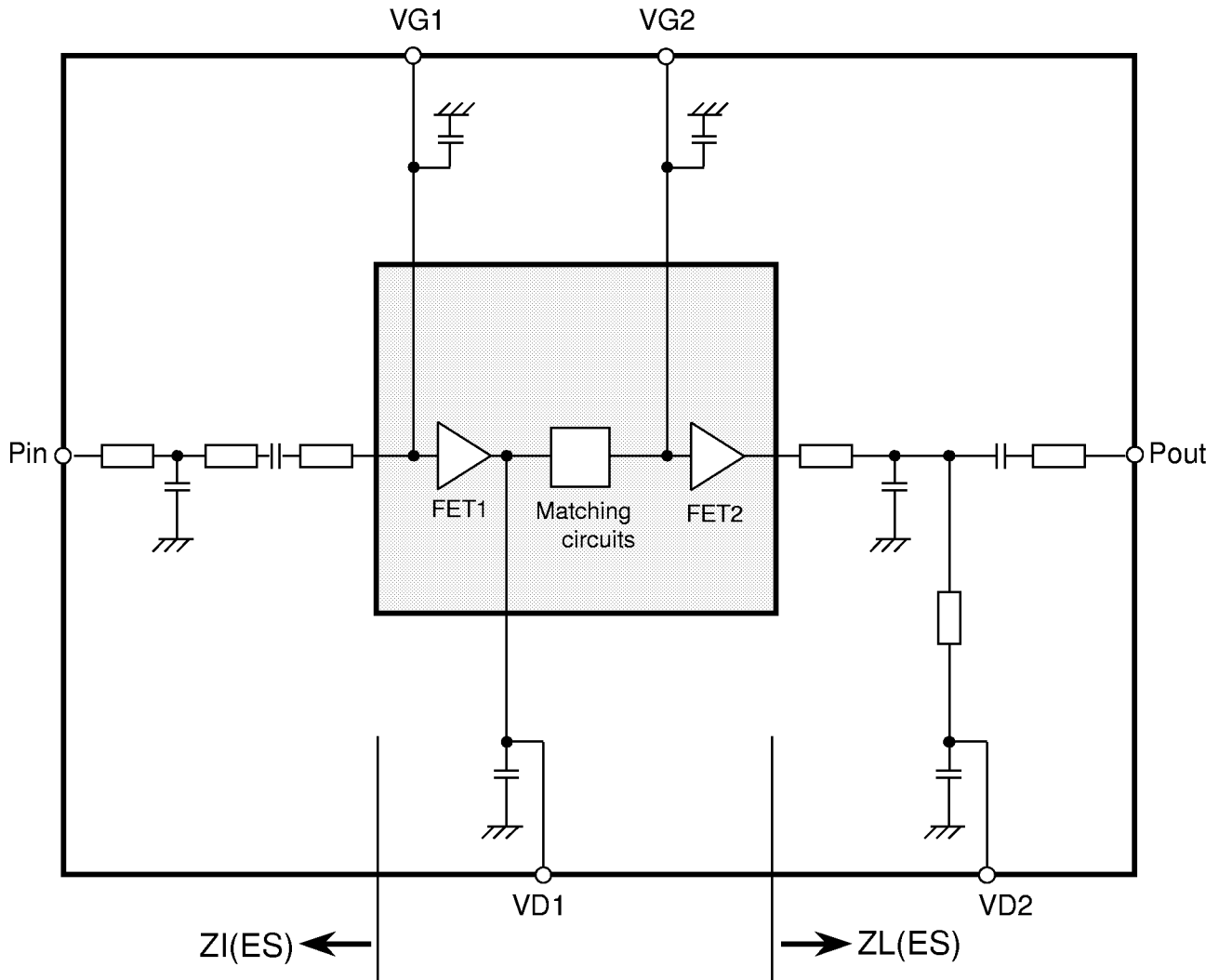
40 x 60 mm

SUB. data
ER=4.8
H=600 μ m
Metal T=43 μ m



Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER



Equivalent circuit of MGF7169C with our test board

-  : MGF7169C(Ceramic package)
-  : our test board($\epsilon_r=4.8$, $t=0.6\text{mm}$)

Preliminary
information

MGF7169C

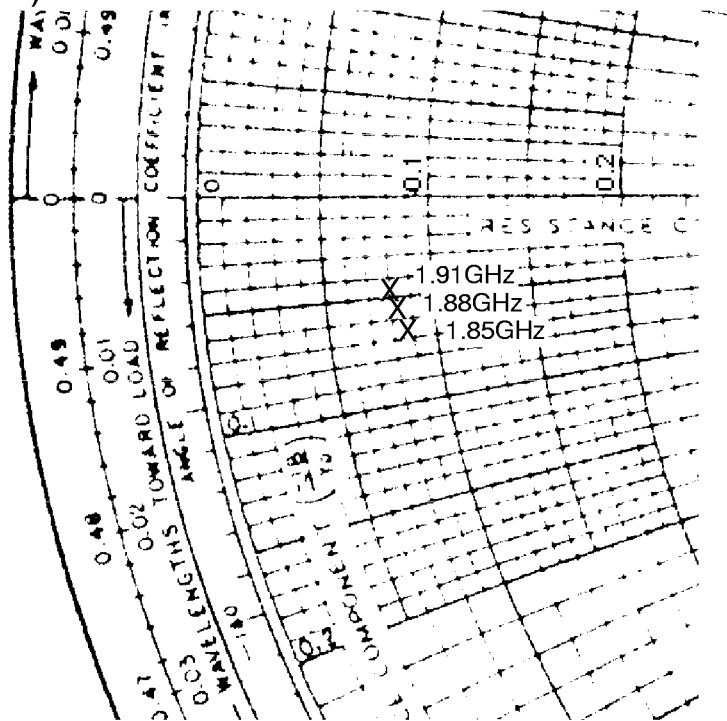
UHF BAND GaAs POWER AMPLIFIER

Input/Output Impedance (@1.85-1.91GHz)

$$\begin{aligned} ZI(ES) &= 6.8 - j22.7 (\Omega) \text{ f}=1.85\text{GHz} \\ &6.7 - j21.3 (\Omega) \text{ f}=1.88\text{GHz} \\ &6.6 - j19.8 (\Omega) \text{ f}=1.91\text{GHz} \end{aligned}$$

$$\begin{aligned} ZL(ES) &= 4.3 - j3.2 (\Omega) \text{ f}=1.85\text{GHz} \\ &4.2 - j2.7 (\Omega) \text{ f}=1.88\text{GHz} \\ &4.0 - j2.3 (\Omega) \text{ f}=1.91\text{GHz} \end{aligned}$$

ZL(ES) on SMITH CHART



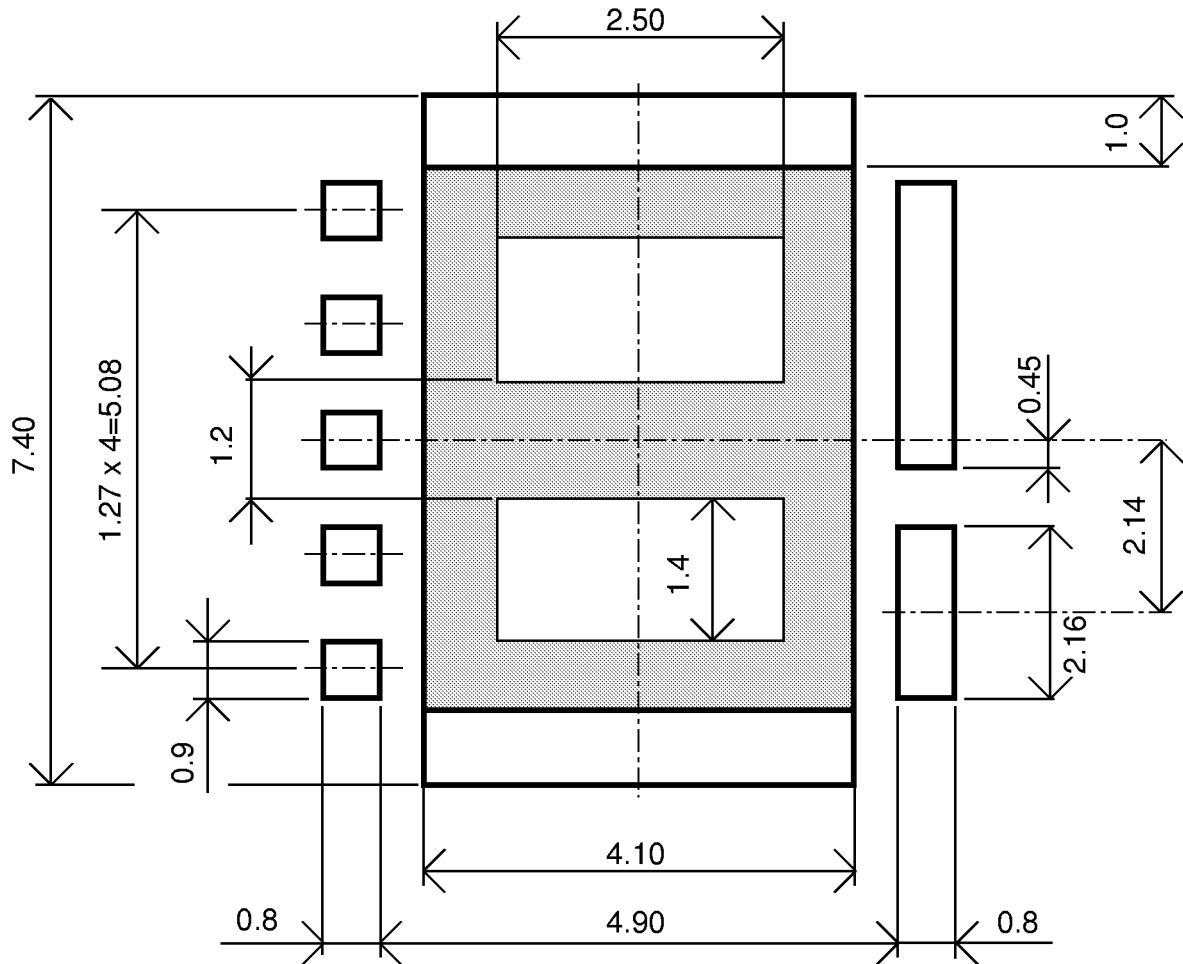
Conditions;
 Vd1=Vd2=3.0V
 Vg1=Vg2=-2.0V
 Pout=28dBm

Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Recommended Mount Pad



Unit:mm

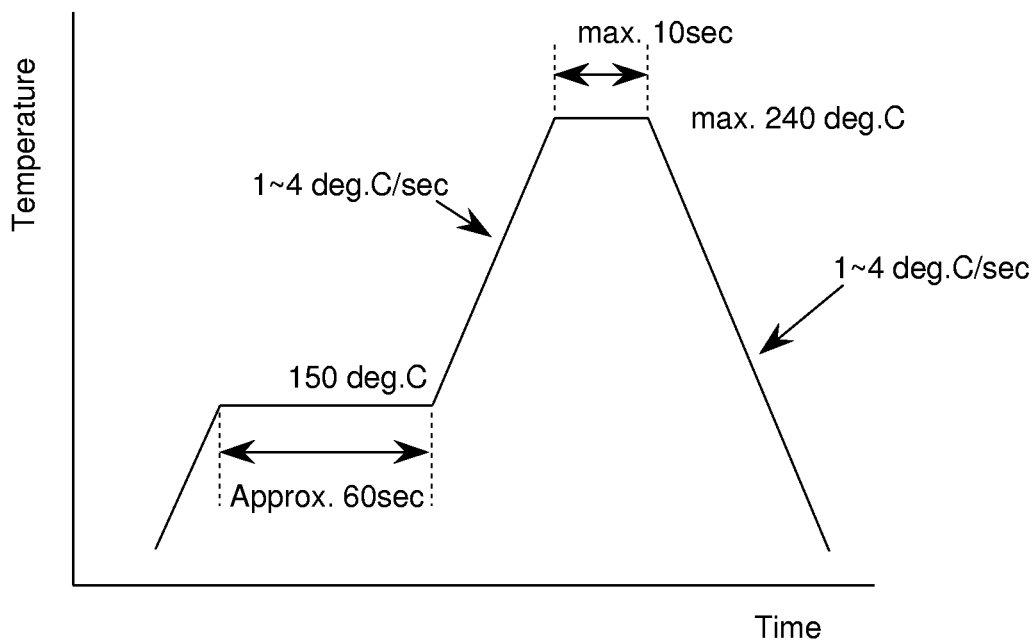
Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Recommended Temperature Profile

1) Infrared Reflow and Air Reflow Temperature Profile



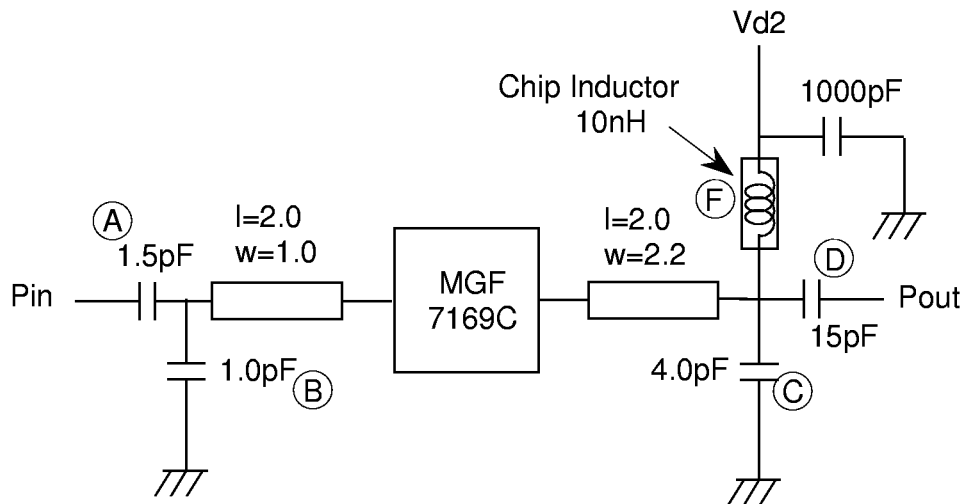
- Notes 1) Temperature profile on package surface
2) Reflow process : Up to three times

Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Lumped Elements Equivalent Circuit of Test Board for CDMA(1.85-1.91GHz)



Unit:mm

SUB. data

Er=4.8

H=600 um

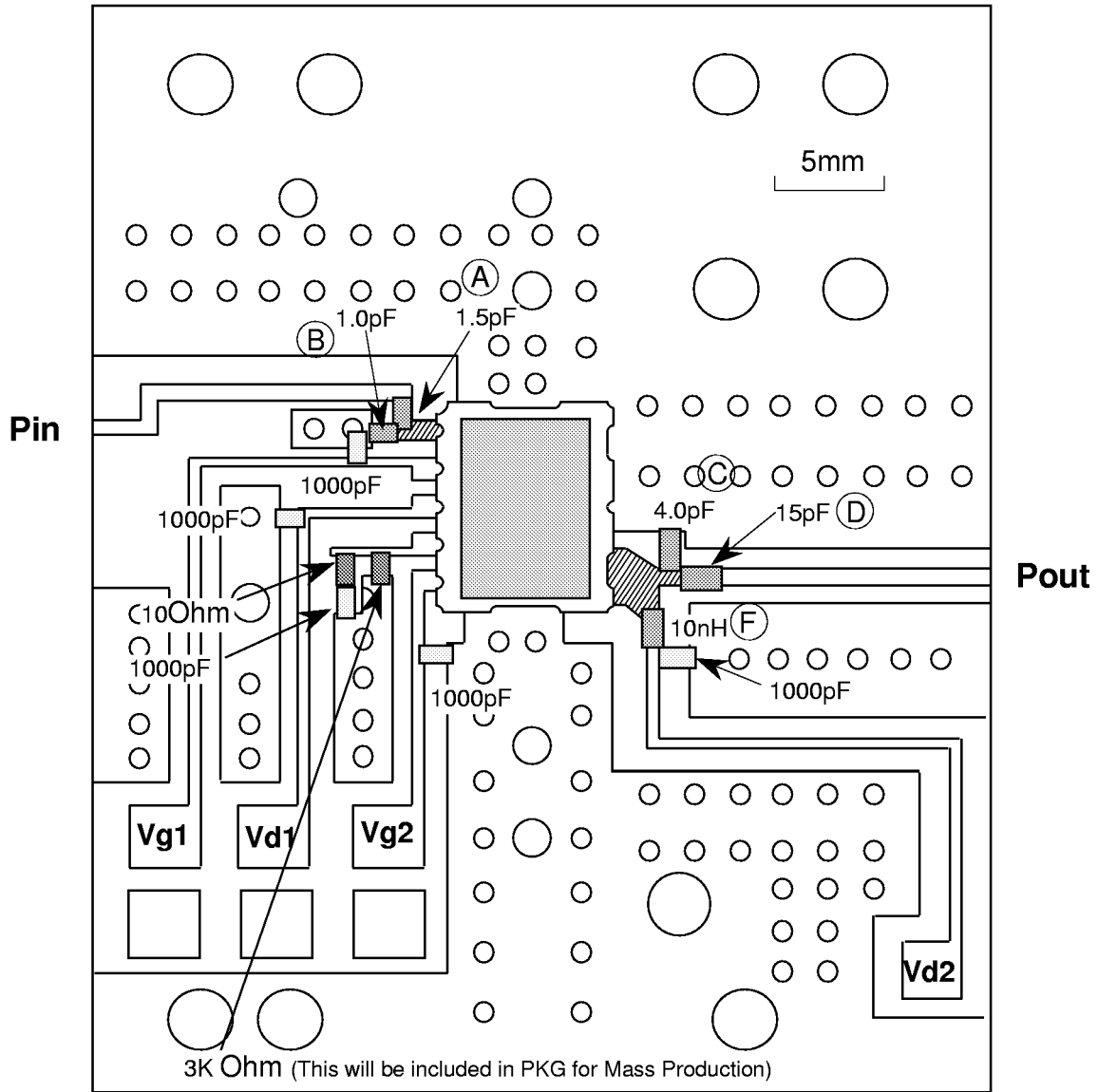
Metal T=43 um

Preliminary
information

MGF7169C

UHF BAND GaAs POWER AMPLIFIER

Lumped Elements Test Circuit Board for CDMA(1.85-1.91GHz)



-  Line
-  Chip Capacitor
-  Chip Inductor

40 x 60 mm

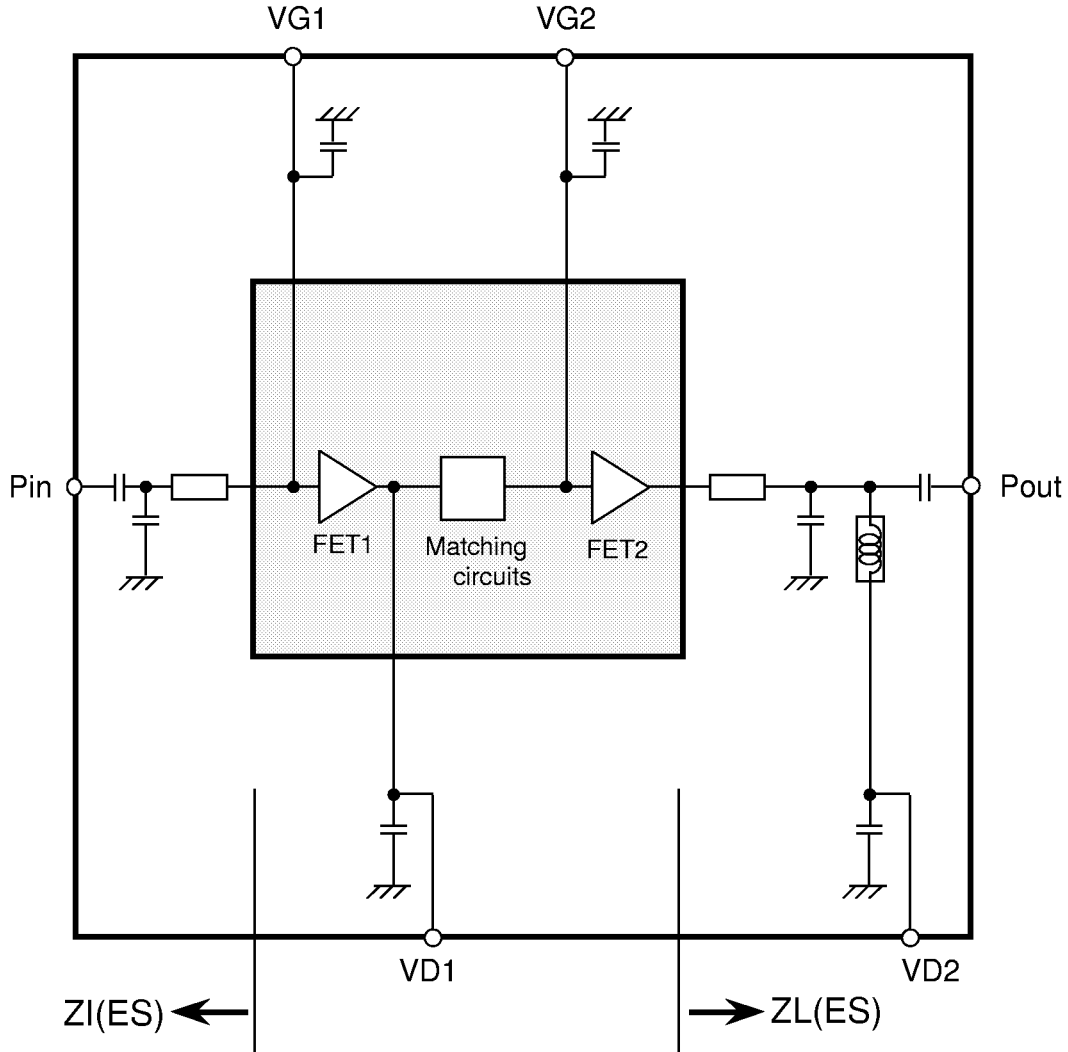
This device needs 4 chip capacitors, 1 chip inductor and 2 transmission lines to make input and output matching circuit.

SUB. data
ER=4.8
H=600um
Metal T=43um

Preliminary
information


MGF7169C

UHF BAND GaAs POWER AMPLIFIER



Lumped Elements

Equivalent circuit of MGF7169C with our test board

 : MGF7169C(Ceramic package)

 : our test board($\epsilon_r=4.8$, $t=0.6\text{mm}$)